

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|------------------|
| L1 | 7164 | 257/E21.277,758-760,762,763,751.ccis. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/11/04 15:28 |
| L2 | 42 | 1 and ((carbon near silicon near oxide) SiOCH) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/11/04 15:44 |
| L3 | 12 | 2 and ((silicon Si) near ("CH.sub.3" CH3)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/11/04 15:45 |
| L4 | 579 | ((carbon near silicon near oxide) SiOCH) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/11/04 15:44 |
| L5 | 51 | 4 and ((silicon Si) near ("CH.sub.3" CH3)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB | OR | ON | 2005/11/04 15:45 |
| L7 | 1 | ((insulat\$3 dielectric) ADJ (layer\$1 film\$1)) AND carbon AND ((silicon Si) ADJ oxide) AND SiOCH AND (Si NEAR CH2) AND bond\$3.CLM. | US-PGPUB; USPAT | OR | ON | 2005/11/04 15:52 |